

ADE-208-319B(Z)

HVM132WK

Silicon Epitaxial Planar Pin Diode for Antenna Switching

HITACHI

Rev. 2
Jan. 1996

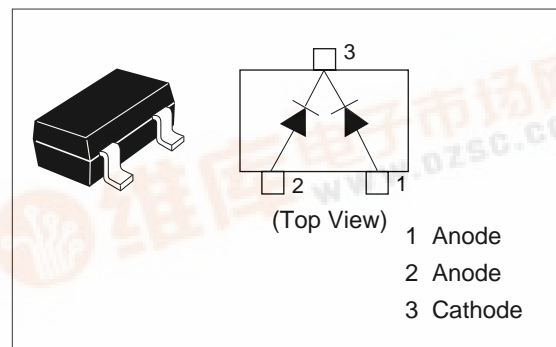
Features

- Low capacitance. ($C=0.5\text{pF}$ max)
- Low forward resistance. ($r_f=2.0\Omega$ max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVM132WK	P4	MPAK

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F^*	100	mA
Power dissipation	P_d^*	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

* Two device total

Electrical Characteristics ($T_a = 25^\circ\text{C}$) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 10\text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 60\text{ V}$
Capacitance	C	—	—	0.5	pF	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$
Forward resistance	r_f	—	—	2.0	Ω	$I_F = 10\text{ mA}$, $f = 100\text{ MHz}$

* Do not guarantee electrical characteristics when forward bias between (1) - (3) or (2) - (3) and reverse bias between (2) - (3) or (1) - (3) at the same time and vice versa.

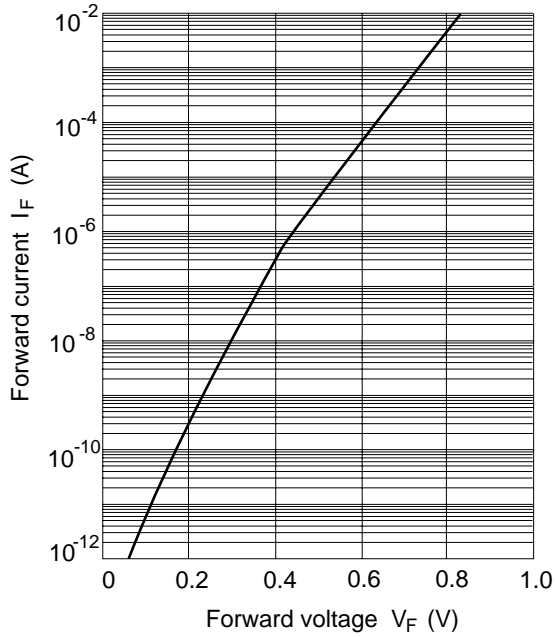


Fig.1 Forward current Vs. Forward voltage

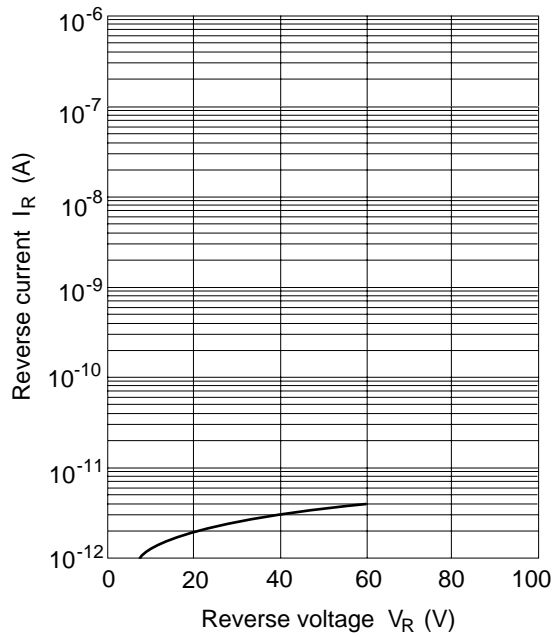


Fig.2 Reverse current Vs. Reverse voltage

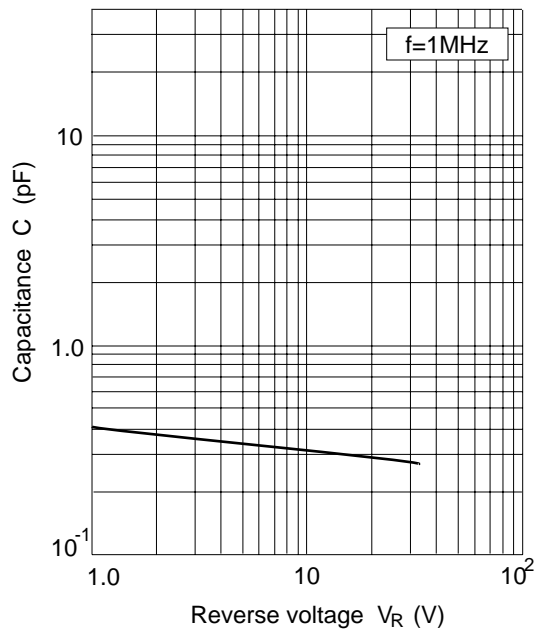


Fig.3 Capacitance Vs. Reverse voltage

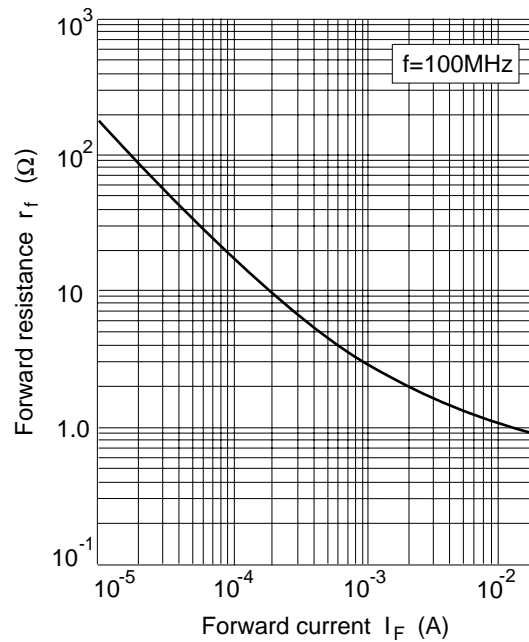


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm

